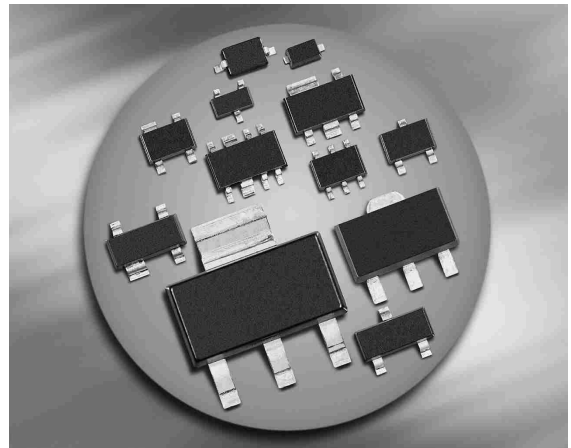
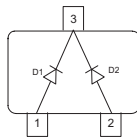
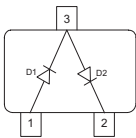


Silicon RF Switching Diode

- Low-loss VHF / UHF switch above 10 MHz
- PIN diode with low forward resistance


BAT18-04
BAT18-05


Type	Package	Configuration	L_S (nH)	Marking
BAT18-04	SOT23	series	1.8	AUs
BAT18-05	SOT23	common cathode	1.8	ASs

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	35	V
Forward current	I_F	100	mA
Junction temperature	T_j	150	°C
Operating temperature range	T_{op}	-55 ... 125	
Storage temperature	T_{stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾ BAT18-04, BAT18-05	R_{thJS}	≤ 290	K/W

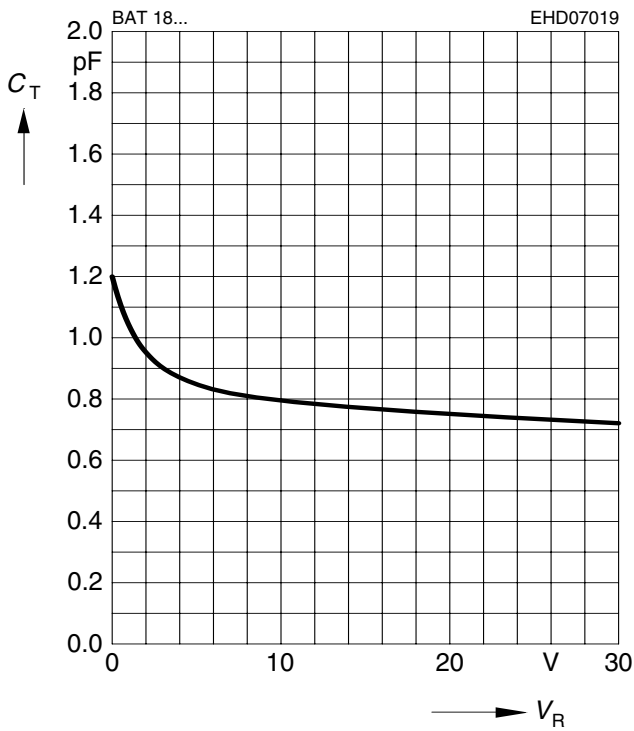
¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current $V_R = 20\text{ V}$ $V_R = 20\text{ V}, T_A = 60^\circ\text{C}$	I_R	- -	- -	20 200	nA
Forward voltage $I_F = 100\text{ mA}$	V_F	-	0.92	1.2	V
AC Characteristics					
Diode capacitance $V_R = 20\text{ V}, f = 1\text{ MHz}$	C_T	-	0.75	1	pF
Forward resistance $I_F = 5\text{ mA}, f = 100\text{ MHz}$	r_f	-	0.4	0.7	Ω
Charge carrier life time $I_F = 10\text{ mA}, I_R = 6\text{ mA}$, measured at $I_R = 3\text{ mA}$, $R_L = 100\ \Omega$	τ_{rr}	-	120	-	ns
I-region width	W_I	-	3	-	μm

Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$



Forward resistance $r_f = f(I_F)$

$f = 100\text{MHz}$

